# PROCESS CP716V

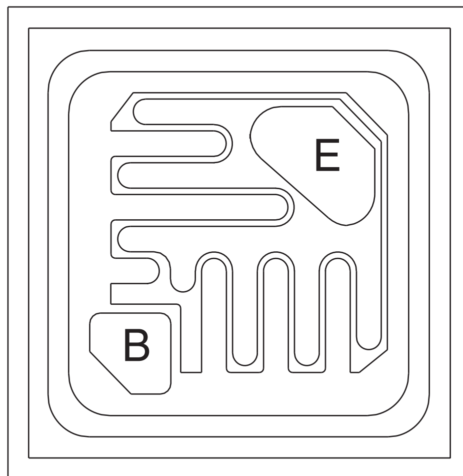
## Small Signal Transistors

### PNP - High Voltage Transistor Chip

**PROCESS DETAILS**

| Process | EPITAXIAL PLANAR |
|---|---|
| Die Size | 19.7 x 19.7 MILS |
| Die Thickness | 7.1 MILS |
| Base Bonding Pad Area | 4.0 x 4.0 MILS |
| Emitter Bonding Pad Area | 4.7 x 4.7 MILS |
| Top Side Metalization | Al - 30,000Å |
| Back Side Metalization | Au - 18,000Å |

**GEOMETRY**




BACKSIDE COLLECTOR R0

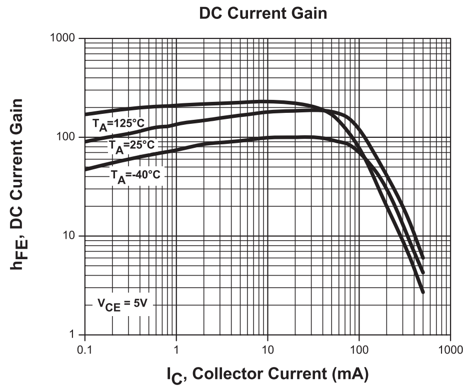
**GROSS DIE PER 4 INCH WAFER**
29,659

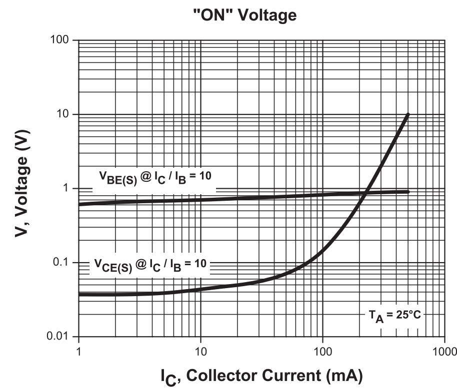
**PRINCIPAL DEVICE TYPES**
CMUT5401
CMPT5401
CXT5401

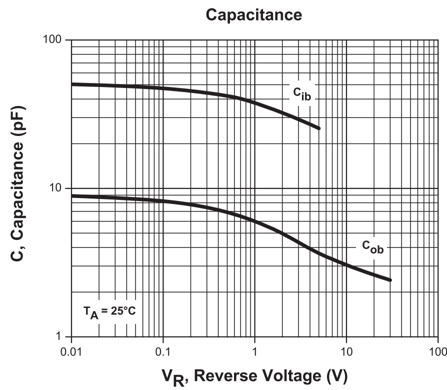
R2 (22-March 2010)

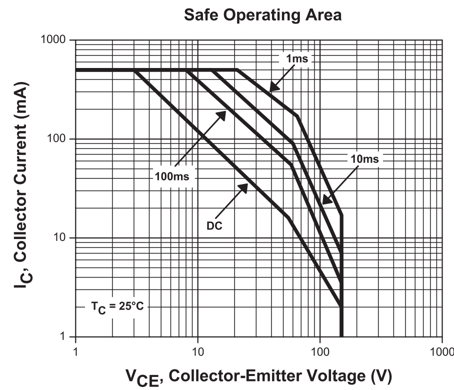
# PROCESS CP716V

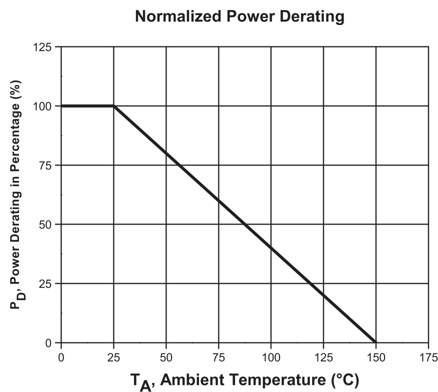
## Typical Electrical Characteristics

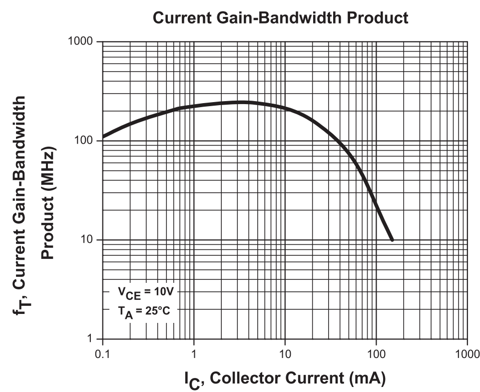



R2 (22-March 2010)